NAND3 Simulation and Layout - Delay Analysis

Vladislav Pomogaev - 26951160

November 14, 2021

1 Problem 1

1.1 Specifications

Here are the specifications for my NAND3 gate: $\,$

• Area: 0.0981 micrometer squared

• Average delay: 25.61 pico-seconds

• Area delay: 2.5130 pico-seconds micrometer squared

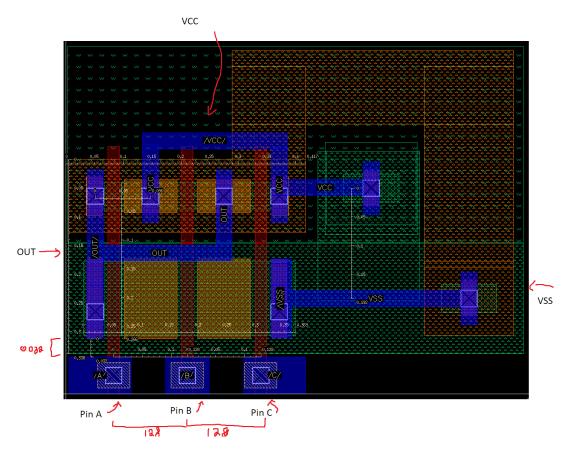


Figure 1: Layout of the gate. I had to add bulk connections otherwise I could not pass LVS for some reason. For the area, I measured the largest dimensions made by the active areas.

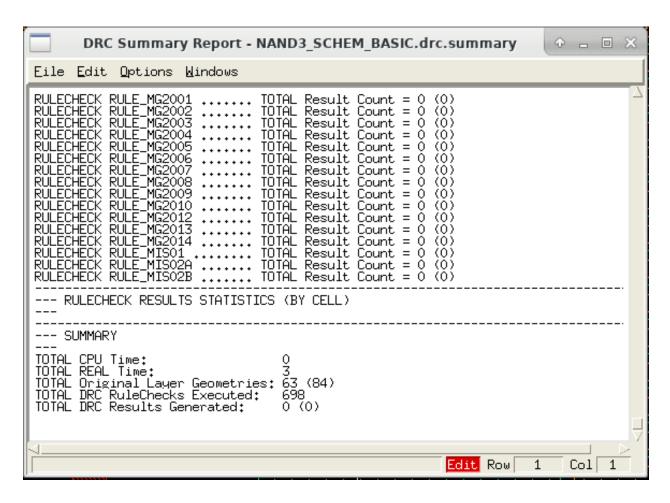


Figure 2: DRC Summary report (I solved the two rule checks that we were allowed to ignore)

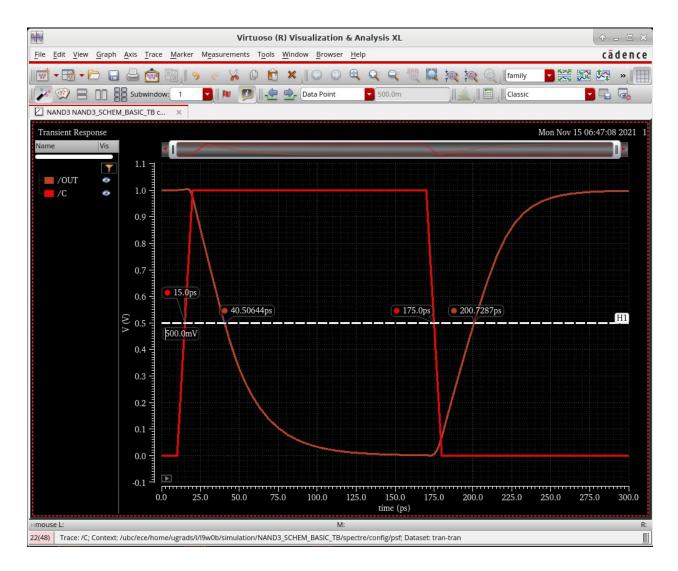


Figure 3: Timing of the gate. $td,HL=25.507ps,\,td,LD=25.72ps.$ This graph was generated from the extracted view including all parasitics.

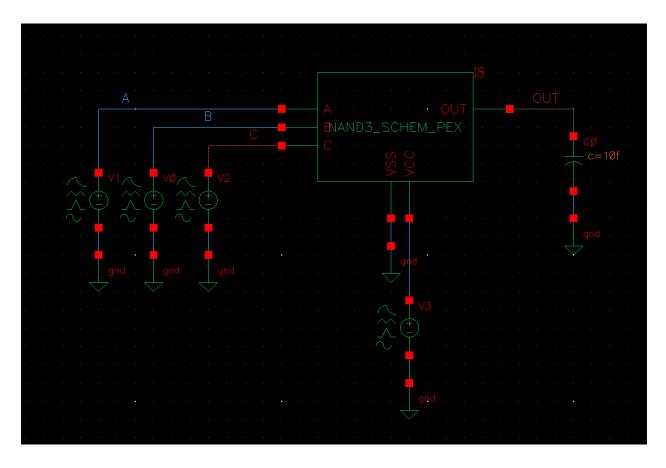


Figure 4: Screen-shot of my test bench schematic. I used a 10pF capacitor as the load. Worst-case switching was used (switching C, aka bottom n-fet results in worst switching).

2 Problem 2

2.1 a)

Using demorgan's law:

$$\overline{F} = CD(B+A)$$

$$\overline{\overline{F}} = \overline{CD(B+A)}$$

$$F = \overline{C} + \overline{D} + \overline{B+A}$$

$$F = \overline{C} + \overline{D} + \overline{BA}$$

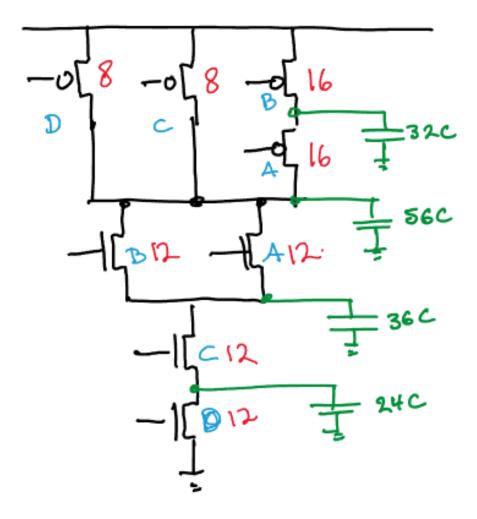


Figure 5: Drawing indicating the sizing of the gates when the output resistance is the same of that of a 8:4 P-N inverter.

2.3 c)

Worst-case		top	1L		Worst	Worst-case EPLH			
time	A	B	C	D	tine O	A	\mathcal{B}	C	Ø
0	1	0	1	0	0	0	1	1	1
1	0	1	1	1	1	Õ	1	1	0

Figure 6: Two tables indicating the worse-case switching conditions for this gate. T=0 is the initial condition, T=1 is the second condition. These switching conditions switch the largest charged capacitances through the largest resistances.

In order to verify that these were in fact the worst-case conditions for this gate, I decided to compare them with what I thought were the second-worst case switching conditions for both t_{PHL} and t_{PLH} . Here are what I think the second worst-case scenarios are.

Second.	-wowst-	case	- to	DHL	Second-worst case Ep 229
bne O 1		0	C 1 1	0	tine A B C D 0 1 0 1 1 4 1 0 1 0

Figure 7: Two tables indicating the **second** worse-case switching conditions for this gate. These conditions switch all but one set of capacitances.

Now I made this circuit in Cadence, and simulated all of the various switching conditions.

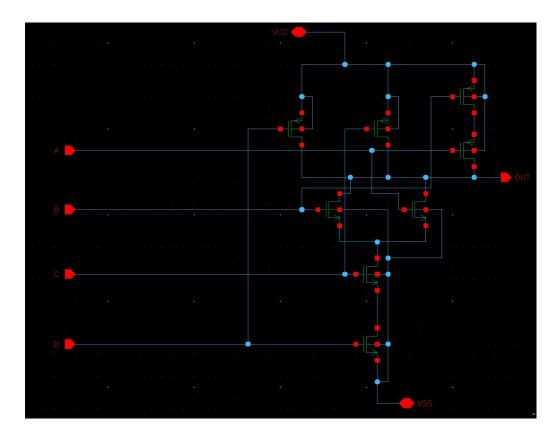


Figure 8: Schematic of the gate.

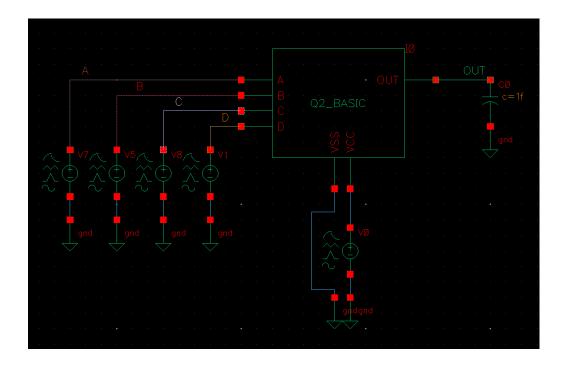


Figure 9: Test bench schematic. The signals generated for A, B, C, and D were generated depending on the test being run. They had a rise time of 0.

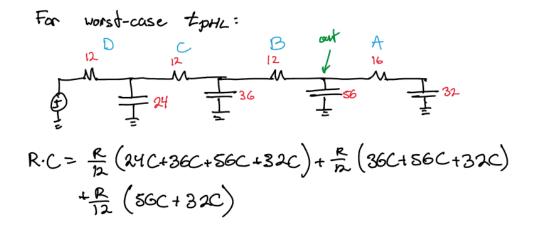


Figure 10: Elmore delay for this circuit, for figuring out worst-case switch conditions.

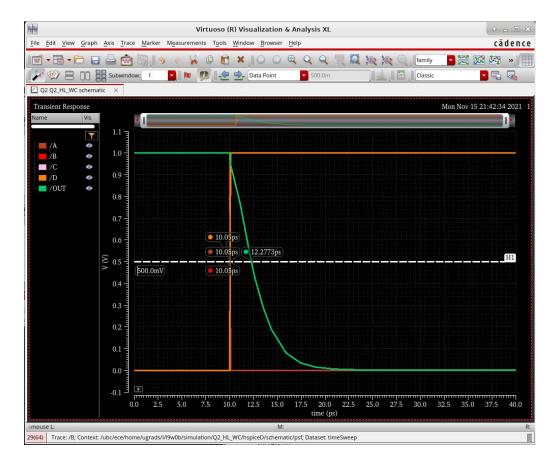


Figure 11: Switching waveform for worst-case t_{PHL} . The switching delay is 2.227ps



Figure 12: Switching waveform for worst-case t_{PLH} . The switching delay is 1.889ps

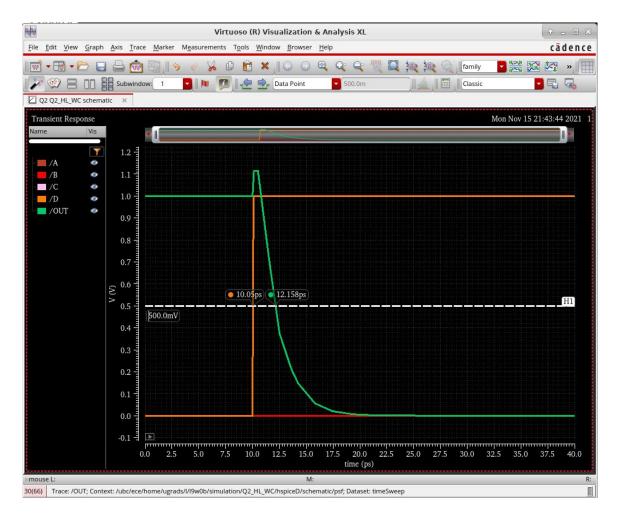


Figure 13: Switching waveform for **second** worst-case t_{PHL} . The switching delay is 2.108ps

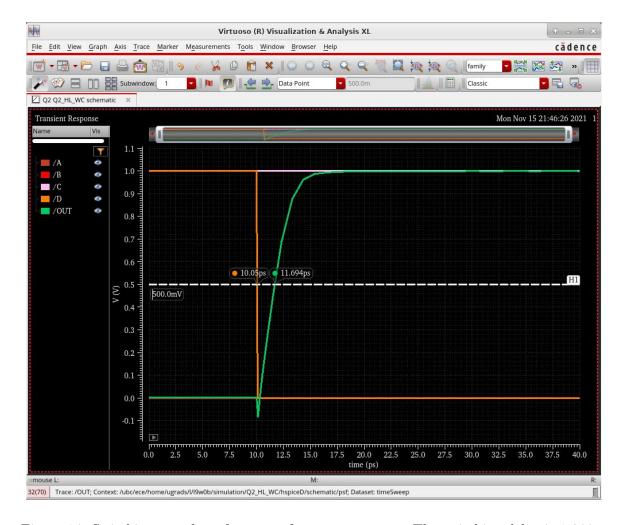


Figure 14: Switching waveform for **second** worst-case t_{PLH} . The switching delay is 1.644ps

Tallying it all up, here are the switching delays:

 $\begin{array}{ccc} & t_{PHL} & t_{PLH} \\ \text{Worst-case} & 2.227 \text{ps} & 1.889 \text{ps} \\ \text{Second-worst-case} & 2.108 \text{ps} & 1.644 \text{ps} \end{array}$

As we can see, the worst-case delay is longer than the second-worst case delay. While this isn't exhaustive proof that we have in fact found the worst-case delay, it serves to reinforce my understanding of where the delays are coming from.

3 Problem 3

3.1 a)

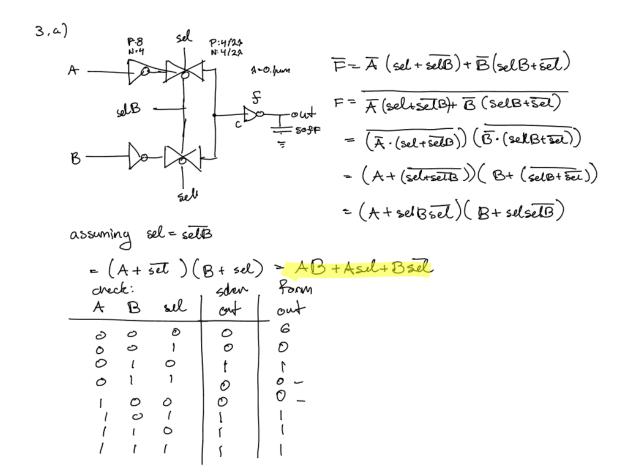


Figure 15: Derivation of the output expression. Here I made the assumption that sel and selB are inverses of each other.

c) using Elmove deday:

$$t = \left(\frac{R^{N}}{2} \left[2C_{g}^{N} | DCeD^{N} + 2C_{g} + 4CeD^{N} \right] + \frac{R^{N}}{2} \left[2C_{g} + 4CeD^{N} \right] \right)$$

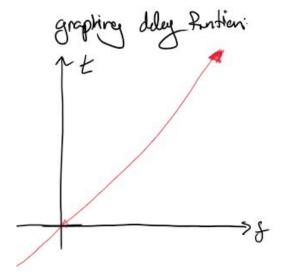
$$= \frac{R}{2} \sqrt{1} \left[4C_{g} + | 4CeD^{N} + 2C_{g} + 4CeD^{N} \right]$$

$$= \frac{R}{2} \sqrt{1} \left[6C_{g} + 8CeD^{N} \right] = R\sqrt{1} \left[3C_{g} + 9CeD^{N} + 6SC_{g} \right]$$

$$= R\sqrt{1} \left[(3+6F)C_{g} + 9CeD^{N} \right]$$

2) optimed size =>
$$\frac{\delta t}{SS}$$
 =0 $t = \ln 2 \cdot (2R)(6SCRH+SOSF)S$ + $R[(3+6F)(g+9CR)]W^2$
 $t = \ln 2 \cdot 2R[6S^2(cR)+(SOSF)S] + R[(3+6F)(g+9CR)]W^2$
 $\frac{\delta t}{\delta t} = \ln 2 \cdot 2R[2SCR) + SOSF] + R \cdot (6Cg = 0)$
 $\left[\frac{-3 \cdot (GW)}{\ln 2} - SOSF \right] \cdot \frac{1}{12 \cdot (cR)} = S$

assuming: $C_{cR} = 1PF/m \cdot G = 2SF/mn \cdot R = 12.5t$
 $S = -4.167$



looks like that
the inverter loads the
gate too much. (>4 times fan)
In order te imprevere
speech it would prebably
make sense to place an inkumediale
ieverter.